

VS-180RKI...PbF, VS-181RKI...PbF Series

Vishay Semiconductors

Phase Control Thyristors (Stud Version), 180 A



PRIMARY CHARACTERISTICS					
I _{T(AV)}	180 A				
V _{DRM} /V _{RRM}	400 V, 800 V, 1000 V				
V _{TM}	1.35 V				
I _{GT}	65 mA				
TJ	-40 °C to +125 °C				
Package	TO-93 (TO-209AB)				
Circuit configuration	Single SCR				

FEATURES

- Hermetic glass-metal seal
- International standard case TO-93 (TO-209AB)

please see www.vishay.com/doc?99912



ROHS COMPLIANT

- Designed and qualified for industrial level
- Material categorization: For definitions of compliance

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS	AND CHARACTERISTICS		
PARAMETER	TEST CONDITIONS	VALUES	UNITS
1		180	A
I _{T(AV)}	T _C	80	°C
I _{T(RMS)}		285	
1	50 Hz	3800	A
ITSM	60 Hz	4000	
l ² t	50 Hz	72	kA ² s
141	60 Hz	66	KA-S
V _{DRM} /V _{RRM}		400 to 1000	V
t _q	Typical	100	μs
TJ		-40 to +125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
PART NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$				
	40	400	500					
VS-180RKI 80 VS-181RKI 100		800	900	30				
		1000	1100					

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ABSOLUTE MAXIMUM RATINGS	5						
PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS	
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduc	ction, half sine w	ave	180 80	A °C	
Maximum RMS on-state current	I _{RMS}	DC at 79 °C	case temperatu	re	285		
		t = 10 ms	No voltage		3800		
Maximum peak, one-cycle non-repetitive surge current		t = 8.3 ms	reapplied		4000	A	
	I _{TSM}	t = 10 ms	100 % V _{RBM}	Sinusoidal half wave, intial $T_J = T_J$ maximum	3500		
		t = 8.3 ms	reapplied		3660		
Maximum I ² t for fusing		t = 10 ms	No voltage		72	kA ² s	
	l ² t	t = 8.3 ms	reapplied		66		
Maximum intro rusing	1-1	t = 10 ms	100 % V _{RRM}		61		
		t = 8.3 ms	reapplied		56		
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to	o 10 ms, no volta	age reapplied	720	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	x I _{T(AV)} < I < π x I	_{T(AV)}), T _J = T _J maximum	0.83	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			v	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.92	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.81	1112.2	
Maximum on-state voltage	V _{TM}	$I_{pk} = 570 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.35	V	
Maximum holding current	Ι _Η	T 25 °C	nodo supply 12	V registive lead	600	m۸	
Typical latching current	١L	J = 25 C, 8	anode supply 12		1000	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \ \mu s$ T_J = T_J maximum, anode voltage $\leq 80 \ \% \ V_{DRM}$	300	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/µs V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	110
Typical turn-off time	tq	I_{TM} = 50 A, T _J = T _J maximum, dl/dt = 10 A/µs, V _R = 100 V, dV/dt = 20 V/µs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM,} I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	30	mA



TR		C 1	D	6
I R	IG	G	= K	G

TRIGGERING							
PARAMETER	SYMBOL		EST CONDITIONS	VAL	UNITS		
FARAIVIETER	STMBOL		EST CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	P _{GM}	$T_J = T_J maximum,$	$t_p \le 5 ms$	1	0	W	
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I _{GM}			3	.0	А	
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J maximum,$	$t_p \le 5 ms$	20		V	
Maximum peak negative gate voltage	- V _{GM}						
		$T_J = -40 \ ^{\circ}C$			-		
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/ current/voltage are the lowest	65	150	mA	
		T _J = 125 °C		35	-		
		T _J = - 40 °C	value which will trigger all units	2.0	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 V anode to cathode applied	1.2	2.5	V	
		T _J = 125 °C		0.9	-	1	
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage not	t 10		mA	
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum	to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation 0.15		K/W	
Maximum thermal resistance, junction to ambient	R _{thCS}	Mounting surface, smooth, flat and greased 0.0		r\/ vv	
Mounting force, ± 10 %		Non-lubricated threads 31 (275)		N·m	
Mounting force, ± 10 %		Lubricated threads24.5 (210)		(lbf · in)	
Approximate weight			280	g	
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-	209AB)	

$\Delta \mathbf{R}_{thJC}$ CONDUCTION	1			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.050	0.032		
120°	0.063	0.059		
90°	0.080	0.082	T _J = T _J maximum	K/W
60°	0.118	0.124		
30°	0.225	0.228		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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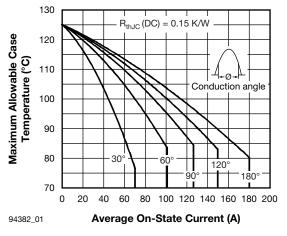


Fig. 1 - Current Ratings Characteristics

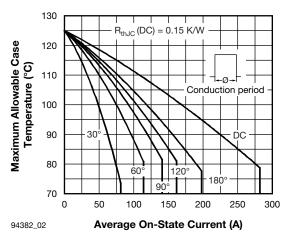
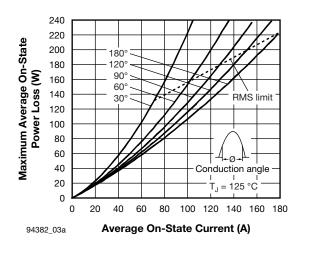
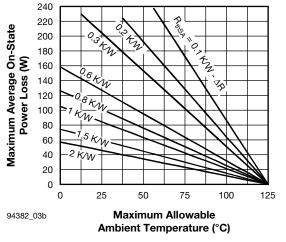
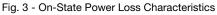
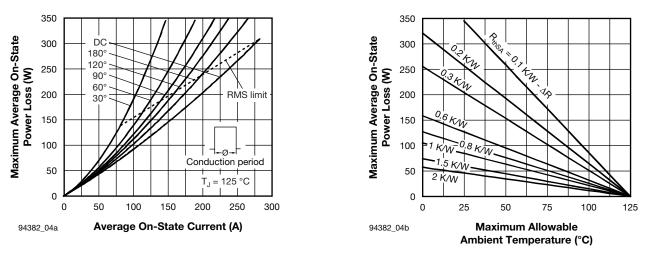


Fig. 2 - Current Ratings Characteristics







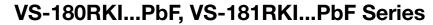




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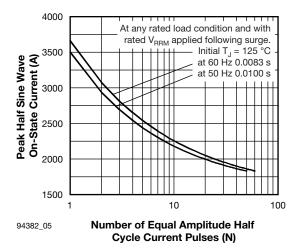
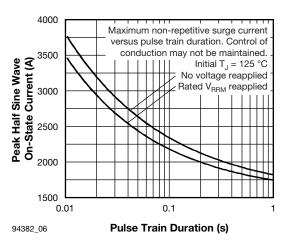
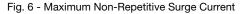


Fig. 5 - Maximum Non-Repetitive Surge Current





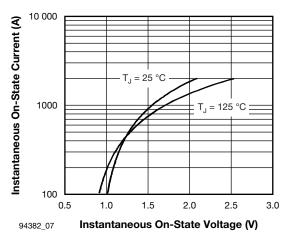
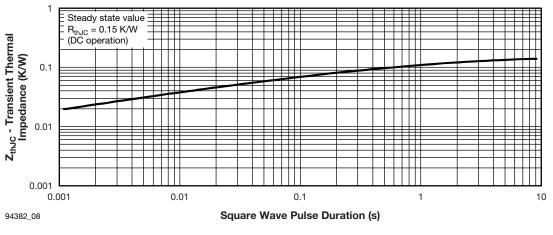


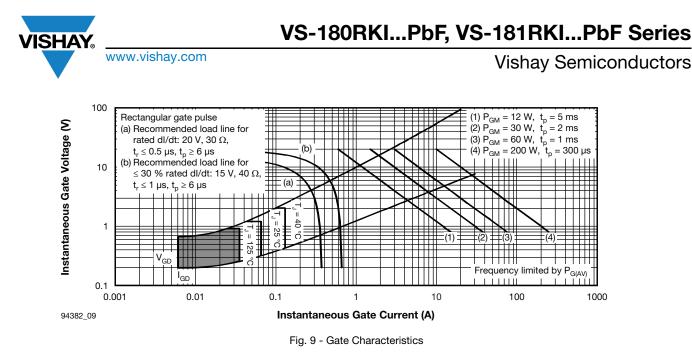
Fig. 7 - On-State Voltage Drop Characteristics





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ORDERING INFORMATION TABLE

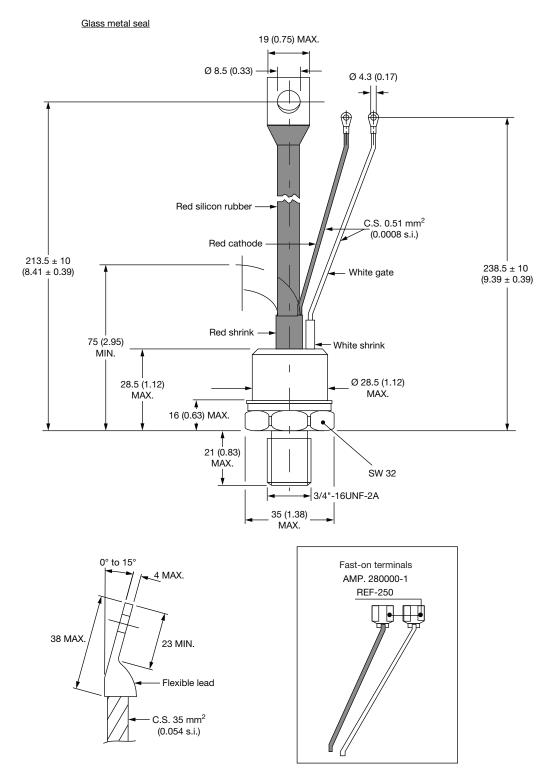
Device code	VS-	18	1	RKI	100	PbF
L. L	1	2	3	4	5	6
	1 - 2 - 3 -	I _{T(A})	n rated a	niconduo average t termina	output	current
ļ	4 - 5 - 6 -	Thy Volt	ristor age coo	on termir de x 10 : tandard	= V _{RRM} ((see Vol
		• Pi	oF = lea	d (Pb)-fı	ee	

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95077			



TO-209AB (TO-93)

DIMENSIONS in millimeters (inches)





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